

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In Re Application Of )  
Ken Takeuchi et al. ) Group Art Unit: 2818  
Divisional of Serial No.: 09/667,610 ) Examiner: H. Ho  
Filed: Herewith )  
For: NONVOLATILE SEMICONDUCTOR ) Atty. Dkt. No. 001701.00140  
MEMORY HAVING PLURAL DATA )  
STORAGE PORTIONS FOR A BIT LINE )  
CONNECTED TO MEMORY CELLS )

The Honorable Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

**PRELIMINARY AMENDMENT**

The Applicants request that the following amendments be entered prior to an action on the merits.

**IN THE TITLE:**

Please delete the existing title in its entirety and replace it with the following Title:

--NONVOLATILE SEMICONDUCTOR MEMORY HAVING PLURAL DATA STORAGE  
PORTIONS FOR A BIT LINE CONNECTED TO MEMORY CELLS--.

**IN THE SPECIFICATION:**

Please insert on line 1, --This application is a Divisional of U.S. Application Serial No.  
09/667,610 filed on September 22, 2000, hereby incorporated by reference as to its entirety.--.

**IN THE CLAIMS:**

Please cancel claims 1-46 and 68-81 without prejudice or disclaimer.

Please amend claims 66 and 67 as follows:


66. (Amended) The nonvolatile semiconductor memory according to claim 65, wherein said fixed potential is a ground potential or a power supply potential.

66. (Amended) The nonvolatile semiconductor memory according to claim 57, wherein said first, second, third and fourth signal lines are bit lines.

**REMARKS**

Applicants request the Examiner consider the above claims prior to an examination on the merits of the present application.

Respectfully Submitted,

By:  Reg. No. 42,338  
for Joseph M. Potenza  
Registration No. 28,175

BANNER & WITCOFF, LTD.  
1001 G Street, N.W., 11<sup>th</sup> Floor  
Washington, D.C. 20001  
(202) 508-9100

Dated: February 14, 2002

**MARKED-UP COPY OF AMENDED CLAIMS**

66. (Amended) The nonvolatile semiconductor memory according to claim [62] 65,

wherein

said fixed potential is a ground potential or a power supply potential.

67. (Amended) The nonvolatile semiconductor memory according to claim [56] 57,

wherein

said first, second, third and fourth signal lines are bit lines.